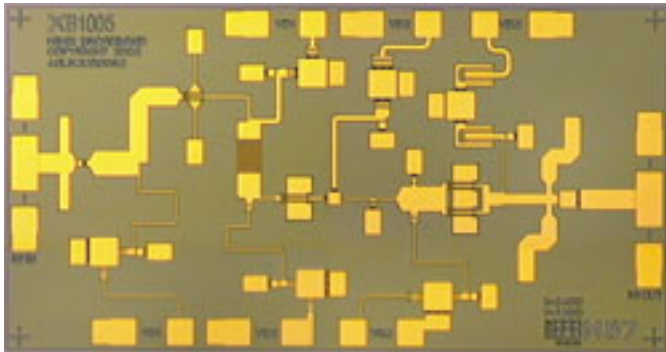


MMIC Amplifier



Mimix Broadband announces a gallium arsenide (GaAs) monolithic microwave integrated circuit (MMIC) three stage buffer amplifier. Using 0.15 micron gate length GaAs pseudomorphic high electron mobility transistor (pHEMT) device model technology, this buffer amplifier covers the 35 to 45 GHz frequency bands. This device can also be operated with all three stages biased in parallel or with independent bias for input and output stages, as required to optimize performance. This MMIC device has a small signal gain of 20 dB with a noise figure of 3 dB across the band. It also has 14 dBm P1dB at low noise bias or can provide 18 dBm P1dB at power bias, with slightly higher gain at power bias. This amplifier, identified as XB1005, serves as an LNA or buffer amplifier, and is suited for wireless communications applications such as millimeter-wave point-to-point radio, local multipoint distribution services (LMDS), SATCOM and VSAT applications.

www.mimixbroadband.com; (281) 988-4600

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